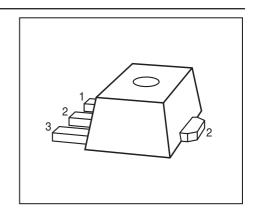


Low Noise Silicon Bipolar RF Transistor

- For low noise, low distortion broadband amplifiers in antenna and telecommunications systems up to 1.5 GHz at collector currents from 10 mA to 70 mA
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BFQ19S	FG	1 = B	2 = C	3 = E	SOT89

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	$V_{\sf CEO}$	15	V	
Collector-emitter voltage	V_{CES}	20		
Collector-base voltage	V_{CBO}	20		
Emitter-base voltage	V_{EBO}	3		
Collector current	I _C	120	mA	
Base current	l _B	12		
Total power dissipation ¹⁾	P _{tot}	1	W	
<i>T</i> _S ≤ 85°C				
Junction temperature	TJ	150	°C	
Ambient temperature	T _A	-65 150		
Storage temperature	T _{Stq}	-65 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	65	K/W

 $^{{}^{1}}T_{\rm S}$ is measured on the collector lead at the soldering point to the pcb

 $^{^2}$ For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V _{(BR)CEO}	15	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0					
Collector-emitter cutoff current	I _{CES}	-	-	10	μΑ
$V_{CE} = 20 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB}$ = 10 V, $I_{\rm E}$ = 0					
Emitter-base cutoff current	I _{EBO}	-	-	100	μΑ
$V_{\rm EB} = 2 \text{ V}, I_{\rm C} = 0$					
DC current gain	h _{FE}	70	100	140	-
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, pulse measured					



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

s otherwise s Symbol	Values			Unit
	min.	typ.	max.	
ng)				
f_{T}	4	5.5	-	GHz
C _{cb}	-	1.05	1.35	pF
C _{ce}	-	0.4	-	
C _{eb}	-	3.9	-	
NF _{min}				dB
	-	1.8	-	
	-	3	-	
G _{ma}				
	-	11.5	-	
	-	7	-	
S _{21e} ²				dB
	-	9.5	-	
	-	4	-	
IP ₃	-	32	-	dBm
P _{-1dB}	-	22	-	
	rg) f _T C _{cb} C _{eb} NF _{min} S _{21e} ²	min. ng) fT 4 C _{cb} - C _{ce} - NF _{min} G _{ma} - IS _{21e} ² IP ₃ -	min. typ. fT 4 5.5 Ccb - 1.05 Cce - 0.4 NFmin - 1.8 Gma - 11.5 IS21e 2 - 9.5 IP3 - 32	min. typ. max. ng) fT 4 5.5 - C _{cb} - 1.05 1.35 C _{ce} - 0.4 - NF _{min} - 1.8 - - 3 - G _{ma} - 11.5 - - 7 - IS _{21e} ² - 9.5 - IP ₃ - 32 -

 $^{{}^{1}}G_{ma} = |S_{21}/S_{12}| (k-(k^{2}-1)^{1/2})$

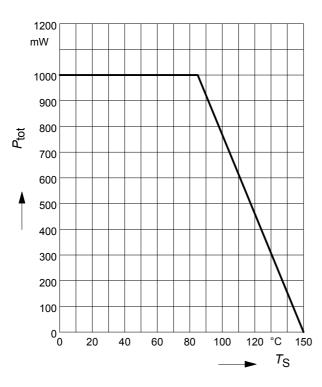
²IP3 value depends on termination of all intermodulation frequency components.

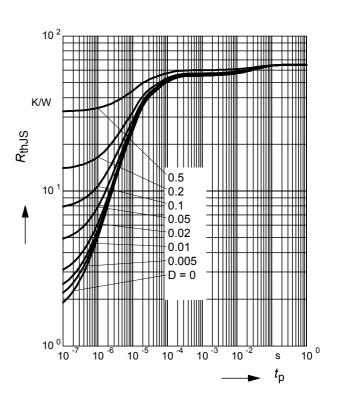
Termination used for this measurement is 50Ω from 0.2 MHz to 12 GHz



Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$

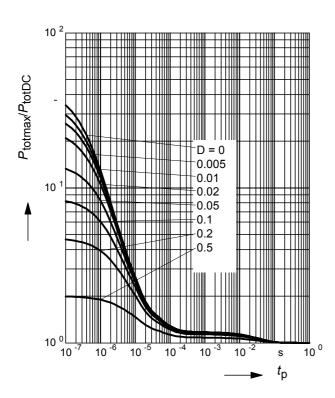
Permissible Pulse Load $R_{thJS} = f(t_p)$





Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$$





SPICE GP model

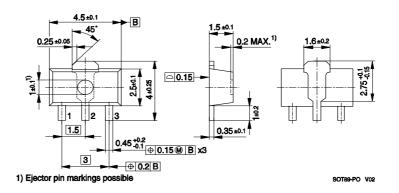
For the SPICE model as well as for S-parameters (including noise parameters) please refer to our internet website www.infineon.com/rf.models. Please consult our website and download the latest versions before actually starting your design.

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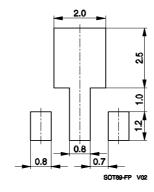


Package Outline

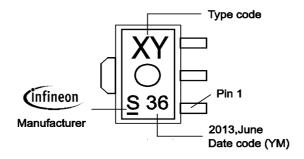




Foot Print

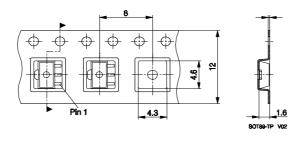


Marking Layout (Example)



Standard Packing

Reel Ø 180 mm= 1.000 Pieces/Reel Reel Ø 330 mm= 4.000 Pieces/Reel





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